# **Quad 2-Input OR Gate**

The MC74VHC32 is an advanced high speed CMOS 2–input OR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

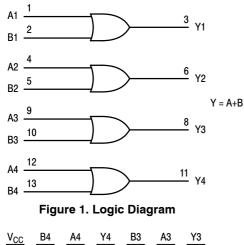
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

### Features

- High Speed:  $t_{PD} = 3.8 \text{ ns} (Typ) \text{ at } V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2.0 \ \mu A \ (Max)$  at  $T_A = 25^{\circ}C$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 48 FETs or 12 Equivalent Gates
- Pb-Free Packages are Available\*



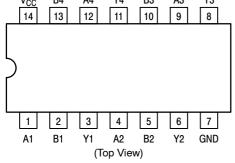
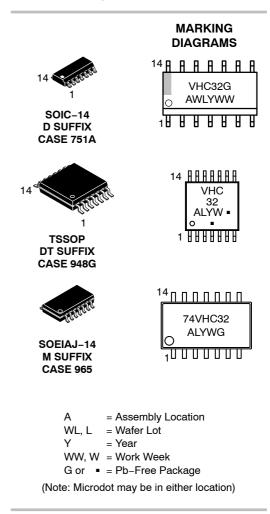


Figure 2. Pinout: 14-Lead Packages



# **ON Semiconductor®**

http://onsemi.com



### FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	L
L	н	н
н	L	н
н	н	Н

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

### MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V	
V <sub>in</sub>	DC Input Voltage	-0.5 to +7.0	V	
V <sub>out</sub>	DC Output Voltage	–0.5 to V <sub>CC</sub> +0.5	V	
I <sub>IK</sub>	Input Diode Current		-20	mA
I <sub>OK</sub>	Output Diode Current		±20	mA
I <sub>out</sub>	DC Output Current, per Pin		±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GNI	) Pins	±50	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages <sup>†</sup> TSSOP Package <sup>†</sup>	500 450	mW
T <sub>stg</sub>	Storage Temperature		-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating – SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage		2.0	5.5	V
V <sub>in</sub>	DC Input Voltage		0	5.5	V
V <sub>out</sub>	DC Output Voltage		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature		-40	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	ns/V

### DC ELECTRICAL CHARACTERISTICS

			V <sub>cc</sub>	T,	<sub>A</sub> = 25°	С	T <sub>A</sub> = −40°0	C to 125°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V <sub>CC</sub> x 0.7			1.50 V <sub>CC</sub> x 0.7		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V <sub>CC</sub> x 0.3		0.50 V <sub>CC</sub> x 0.3	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4.0 \text{ mA}$ $I_{OH} = -8.0 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4.0 \text{ mA}$ $I_{OL} = 8.0 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μΑ
Icc	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5			2.0		20.0	μΑ

### AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$ )

				T <sub>A</sub> = 25°C		T <sub>A</sub> = −40°C to 125°C		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay,	$\begin{array}{c} V_{CC} = 3.3 \pm 0.3 \ \text{VC}_L = 15 \ \text{pF} \\ C_L = 50 \ \text{pF} \end{array}$		5.5 8.0	7.9 11.4	1.0 1.0	9.5 13.0	ns
	A or B to Y	$\label{eq:VCC} \begin{array}{l} V_{CC} = 5.0 \pm 0.5 \; V  C_L = 15 \; pF \\ C_L = 50 \; pF \end{array}$		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5	
C <sub>in</sub>	Maximum Input Capacitance			4	10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Note 1)	14	pF

1.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/4$  (per gate).  $C_{PD}$  is used to determine the no-load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

			T <sub>A</sub> = 25°C	
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V

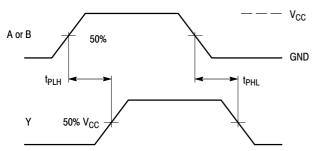
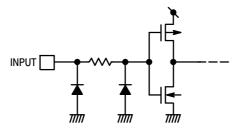
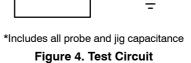


Figure 3. Switching Waveforms





DEVICE

UNDER

TEST

OUTPUT

TEST POINT

CL\*

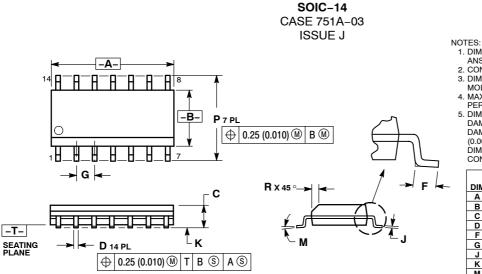
Figure 5. Input Equivalent Circuit

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74VHC32DR2	SOIC-14	2500 Units / Tape & Reel
MC74VHC32DR2G	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel
MC74VHC32DT	TSSOP-14*	96 Units / Rail
MC74VHC32DTG	TSSOP-14*	96 Units / Rail
MC74VHC32DTR2	TSSOP-14*	2500 Units / Tape & Reel
MC74VHC32DTR2G	TSSOP-14*	2500 Units / Tape & Reel
MC74VHC32MELG	SOEIAJ-14 (Pb-Free)	2000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 \*This package is inherently Pb-Free.

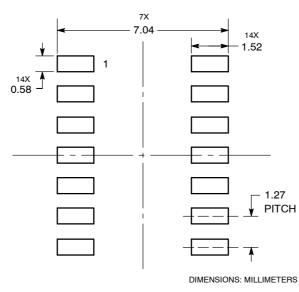
### PACKAGE DIMENSIONS



NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

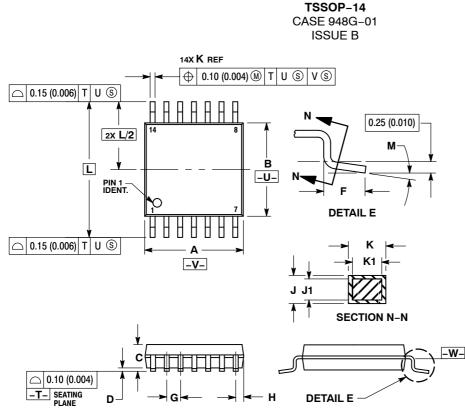
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
κ	0.10	0.25	0.004	0.009
М	0 °	7 °	0 °	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

#### SOLDERING FOOTPRINT



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

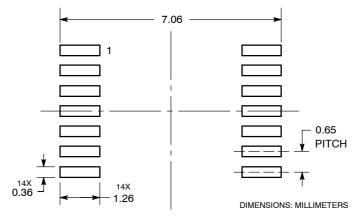


- NOTES: 1. DIMENSIONING AND TOLERANCING PER
  - DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
    CONTROLLING DIMENSION: MILLIMETER.
    DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
    MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
    DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
    INTERLEAD FLASH OR PROTRUSION.
    INTERLEAD FLASH OR PROTRUSION.
    INTERLEAD FLASH OR PROTRUSION.
    DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE
    DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
- CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR

REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE

PETE			FUM PL	<del>ANE –</del> M
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
Μ	0 °	8 °	0 °	8 °

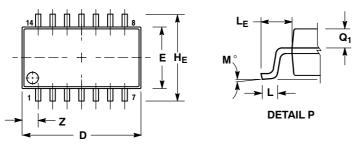
SOLDERING FOOTPRINT

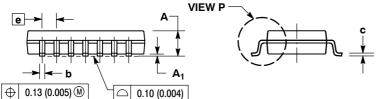


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 ISSUE B





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.

- CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE. 4. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003)

TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
A <sub>1</sub>	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
C	0.10	0.20	0.004	0.008	
D	9.90	10.50	0.390	0.413	
E	5.10	5.45	0.201	0.215	
e	1.27 BSC		0.050	) BSC	
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
Μ	0 °	10 °	0 °	10 °	
Q1	0.70	0.90	0.028	0.035	
Z		1.42		0.056	

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